

AMENDMENT TO THE CLAIMS:

1-9. (Canceled)

10. (Original) A thin film transistor comprising a semiconductor film, a first gate insulating film, a second gate insulating film and a gate electrode sequentially formed on one major surface of a substrate in that order,

wherein said first gate insulating film covers said semiconductor film, and

said second gate insulating film is made of a material for supplying hydrogen to said semiconductor film,

said second gate insulating film is integrally formed over said first gate insulating film, which covers the semiconductor film, and

said second gate insulating film has a smaller film thickness in a region not covered with said gate electrode than that in a region covered with said gate electrode.

11. (Original) The thin film transistor according to claim 10, wherein said first gate insulating film is a silicon oxide film and said second gate insulating film is a silicon nitride film.

12. (Original) The thin film transistor according to claim 10, wherein said semiconductor film is a poly-silicon film.